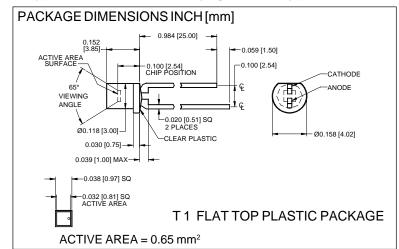
**PHOTONIC** Silicon Photodiode, Blue Enhanced Photoconductive **DETECTORS INC.** Type PDB-C131, with daylight filter Type PDB-C131F





### **FEATURES**

- Photoconductive
- High speed
- Low cost
- Flat top, T1 package

**DESCRIPTION:** The **PDB-C131** detector is a 0.65 mm<sup>2</sup> planar pin photodiode packaged in a T1 flat top, water clear plastic housing. Designed for high speed, low capacitance, photoconductive applications. The **PDB-C131F** includes a daylight filter.

#### **APPLICATIONS**

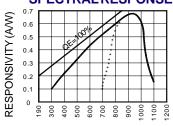
- Smoke detectors
- Light pen detectors
- TV & VCR remotes
- IRDA sensor

# ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
$V_{BR}$	Reverse Voltage		100	V
T <sub>STG</sub>	Storage Temperature	-40	+100	∘C
T <sub>o</sub>	Operating Temperature Range	-40	+80	∘C
T <sub>s</sub>	Soldering Temperature*		+260	∘C
I <sub>L</sub>	Light Current		0.5	mA

<sup>\*1/16</sup> inch from case for 3 secs max

## **SPECTRAL RESPONSE**



WAVELENGTH (nm)

# ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

(17.1—20 ° chiloco chilorwice notod)								
SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS		
I <sub>sc</sub>	Short Circuit Current	H = 100 fc, 2850 K	8	10		μΑ		
I <sub>D</sub>	Dark Current	H = 0, V <sub>R</sub> = 10 V		2	10	nA		
R <sub>SH</sub>	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	.5	5		GΩ		
TCR <sub>SH</sub>	RSH Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		%/°C		
C <sub>J</sub>	Junction Capacitance	H = 0, V <sub>R</sub> = 10 V*		2	5	pF		
λrange	Spectral Application Range	(without daylight filter)**	400		1100	nm		
λр	Spectral Response - Peak			950		nm		
V <sub>BR</sub>	Breakdown Voltage	I = 10 μA	50	100		V		
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 V @ Peak		1.5x10 <sup>-13</sup>		W/ √Hz		
tr	Response Time	$RL = 1 K\Omega V_{p} = 10 V$		5		nS		